November 1994

54F/74F20 Dual 4-Input NAND Gate

General Description

This device contains two independent gates, each of which performs the logic NAND function.

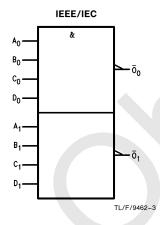
Commercial	Military	Package Number	Package Description		
74F20PC		N14A	14-Lead (0.300" Wide) Molded Dual-In-Line		
	54F20DM (Note 2)	J14A	14-Lead Ceramic Dual-In-Line		
74F20SC (Note 1)		M14A	14-Lead (0.150" Wide) Molded Small Outline, JEDEC		
74F20SJ (Note 1)		M14D	14-Lead (0.300" Wide) Molded Small Outline, EIAJ		
	54F20FM (Note 2)	W14B	14-Lead Cerpack		
	54F20LM (Note 2)	E20A	20-Lead Ceramic Leadless Chip Carrier, Type C		

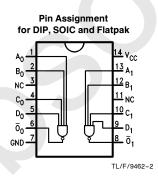
Note 1: Devices also available in 13" reel. Use suffix = SCX and SJX.

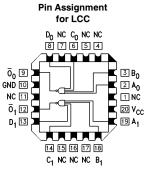
Note 2: Military grade device with environmental and burn-in processing. Use suffix = DMQB, FMQB and LMQB.

Logic Symbol

Connection Diagrams







TL/F/9462-1

Unit Loading/Fan Out

		54F/74F				
Pin Names	Description	U.L. HIGH/LOW	Input I _{IH} /I _{IL} Output I _{OH} /I _{OL}			
A_n, B_n, C_n, D_n \overline{O}_n	Inputs Outputs	1.0/1.0 50/33.3	20 μA/-0.6 mA -1 mA/20 mA			

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RRD-B30M75/Printed in U. S. A.

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

 $\begin{array}{lll} \mbox{Storage Temperature} & -65^{\circ}\mbox{C to} + 150^{\circ}\mbox{C} \\ \mbox{Ambient Temperature under Bias} & -55^{\circ}\mbox{C to} + 125^{\circ}\mbox{C} \\ \mbox{Junction Temperature under Bias} & -55^{\circ}\mbox{C to} + 175^{\circ}\mbox{C} \\ \mbox{Plastic} & -55^{\circ}\mbox{C to} + 150^{\circ}\mbox{C} \\ \end{array}$

V_{CC} Pin Potential to

 Ground Pin
 −0.5V to +7.0V

 Input Voltage (Note 2)
 −0.5V to +7.0V

 Input Current (Note 2)
 −30 mA to +5.0 mA

Voltage Applied to Output in HIGH State (with $V_{CC} = 0V$)

 $\begin{array}{ll} \text{Standard Output} & -0.5 \text{V to V}_{\text{CC}} \\ \text{TRI-STATE} \tiny{\textcircled{\tiny{\$}}} \text{ Output} & -0.5 \text{V to } +5.5 \text{V} \end{array}$

Current Applied to Output in LOW State (Max)

twice the rated I_{OL} (mA)

Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

Recommended Operating Conditions

Free Air Ambient Temperature

 $\begin{array}{ll} \mbox{Military} & -55\mbox{°C to} + 125\mbox{°C} \\ \mbox{Commercial} & 0\mbox{°C to} + 70\mbox{°C} \\ \end{array}$

Supply Voltage

Military +4.5V to +5.5V Commercial +4.5V to +5.5V

DC Electrical Characteristics

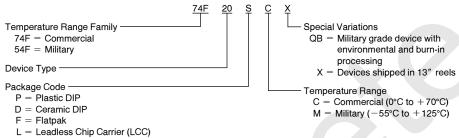
Symbol	Parameter		54F/74F			Units	V _{CC}	Conditions	
			Min	Тур	Max	Oilles	VCC	Conditions	
V_{IH}	Input HIGH Voltage		2.0			V		Recognized as a HIGH Signal	
V_{IL}	Input LOW Voltage				0.8	V		Recognized as a LOW Signal	
V_{CD}	Input Clamp Diode Voltage				-1.2	V	Min	$I_{\text{IN}} = -18 \text{mA}$	
V _{OH}	Output HIGH Voltage	54F 10% V _{CC} 74F 10% V _{CC} 74F 5% V _{CC}	2.5 2.5 2.7			V	Min	$I_{OH} = -1 \text{ mA}$ $I_{OH} = -1 \text{ mA}$ $I_{OH} = -1 \text{ mA}$	
V _{OL}	Output LOW Voltage	54F 10% V _{CC} 74F 10% V _{CC}			0.5 0.5	V	Min	$I_{OL} = 20 \text{ mA}$ $I_{OL} = 20 \text{ mA}$	
I _{IH}	Input HIGH Current	54F 74F			20.0 5.0	μΑ	Max	V _{IN} = 2.7V	
I _{BVI}	Input HIGH Current Breakdown Test	54F 74F			100 7.0	μΑ	Max	V _{IN} = 7.0V	
I _{CEX}	Output HIGH Leakage Current	54F 74F			250 50	μΑ	Max	$V_{OUT} = V_{CC}$	
V _{ID}	Input Leakage Test	74F	4.75			٧	0.0	$I_{\text{ID}} = 1.9 \mu\text{A}$ All other pins grounded	
I _{OD}	Output Leakage Circuit Current	74F			3.75	μΑ	0.0	V _{IOD} = 150 mV All other pins grounded	
I _{IL}	Input LOW Current				-0.6	mA	Max	V _{IN} = 0.5V	
I _{OS}	Output Short-Circuit C	urrent	-60		-150	mA	Max	V _{OUT} = 0V	
I _{CCH}	Power Supply Current			0.9	1.4	mA	Max	V _O = HIGH	
I _{CCL}	Power Supply Current			3.4	5.1	mA	Max	$V_O = LOW$	

AC Electrical Characteristics

Symbol	Parameter	74F			5-	4F	74F		
		$egin{array}{ll} T_{A} = +25^{\circ}C \ V_{CC} = +5.0V \ C_{L} = 50 \ pF \end{array}$			$ extsf{T}_{ extsf{A}}, extsf{V}_{ extsf{CC}} = extsf{Mil} \ extsf{C}_{ extsf{L}} = extsf{50 pF}$		T _A , V _{CC} = Com C _L = 50 pF		Units
		Min	Тур	Max	Min	Max	Min	Max	
t _{PLH}	Propagation Delay	2.4	3.7	5.0	2.0	7.0	2.4	6.0	ne
t_{PHL}	A_n , B_n , C_n , D_n to \overline{O}_n	1.5	3.2	4.3	1.5	6.5	1.5	5.3	ns

Ordering Information

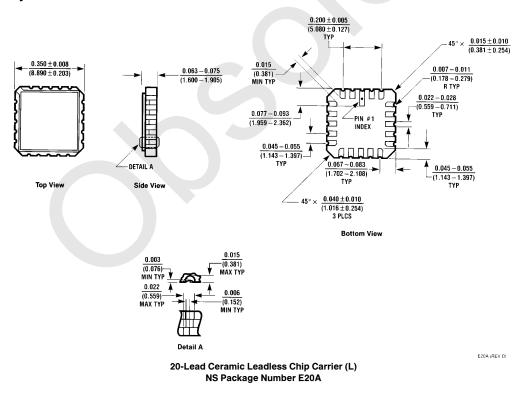
The device number is used to form part of a simplified purchasing code where the package type and temperature range are defined as follows:

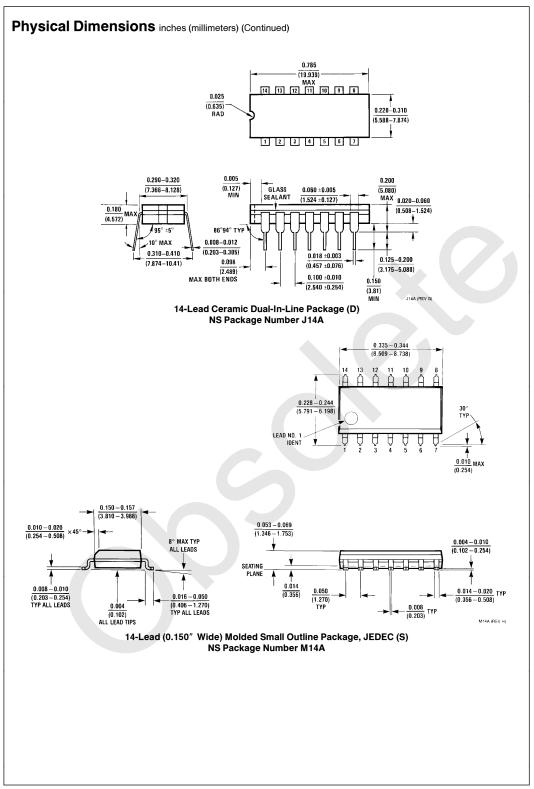


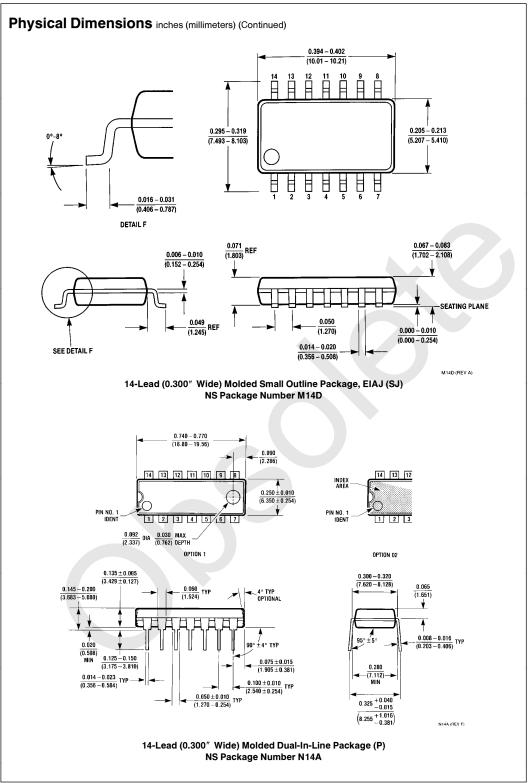
S = Small Outline SOIC JEDEC

SJ = Small Outline SOIC EIAJ

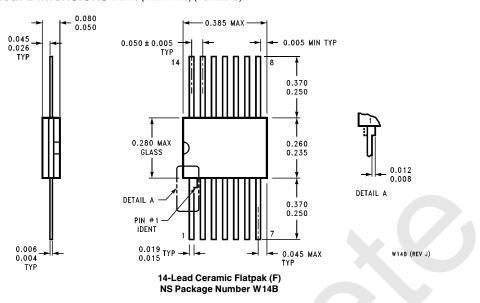
Physical Dimensions inches (millimeters)







Physical Dimensions inches (millimeters) (Continued)



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